

Inchange Semiconductor

Product Specification

Silicon PNP Power Transistors

2SB1054

DESCRIPTION

- With TO-3PFa package
- Complement to type 2SD1485
- High transition frequency
- Wide area of safe operation

APPLICATIONS

- For high power amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

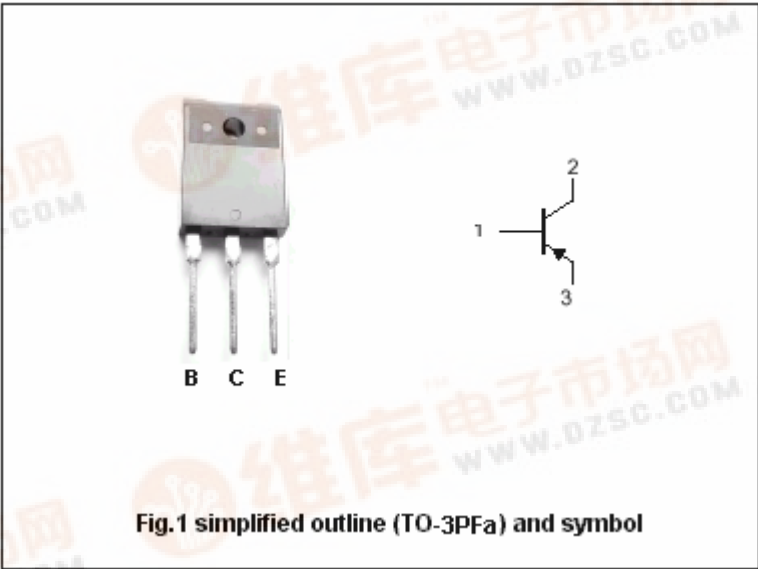


Fig.1 simplified outline (TO-3PFa) and symbol

Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-100	V
V _{CEO}	Collector-emitter voltage	Open base	-100	V
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current		-5	A
I _{CP}	Collector current-peak		-8	A
P _C	Collector power dissipation	T _C =25	60	W
		T _a =25	3	
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-55~150	



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CHARACTERISTICS

Tj=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-3A ; I_B=-0.3A$			-2.0	V
V_{BE}	Base-emitter on voltage	$I_C=-3A ; V_{CE}=-5V$			-1.8	V
I_{CBO}	Collector cut-off current	$V_{CB}=-100V ; I_E=0$			-50	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=-3V ; I_C=0$			-50	μA
h_{FE-1}	DC current gain	$I_C=-20mA ; V_{CE}=-5V$	20			
h_{FE-2}	DC current gain	$I_C=-1A ; V_{CE}=-5V$	40		200	
h_{FE-3}	DC current gain	$I_C=-3A ; V_{CE}=-5V$	20			
C_{OB}	Output capacitance	$I_E=0 ; V_{CB}=-10V ; f=1MHz$		170		pF
f_T	Transition frequency	$I_C=-0.5A ; V_{CE}=-5V$		20		MHz

◆ h_{FE-2} classifications

R	Q	P
40-80	60-120	100-200

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PACKAGE OUTLINE

